# 2SC3829

### Silicon NPN epitaxial planar type

For UHF band low-noise amplification

#### Features

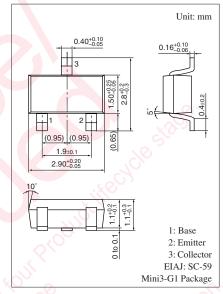
- Low noise figure NF
- High gain
- High forward transfer gain  $|S_{21e}|^2$

Abaaluta Maximum Datinga

• Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing

2500

Absolute Maximum Ratings $T_a = 25^{\circ}$ C								
Parameter	Symbol	Rating	Unit					
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	15	V					
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	10	V					
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	2	v					
Collector current	I <sub>C</sub>	80	mA					
Collector power dissipation	P <sub>C</sub>	200	mW					
Junction temperature	Tj	150	°C					
Storage temperature	T <sub>stg</sub>	-55 to +150	°C					



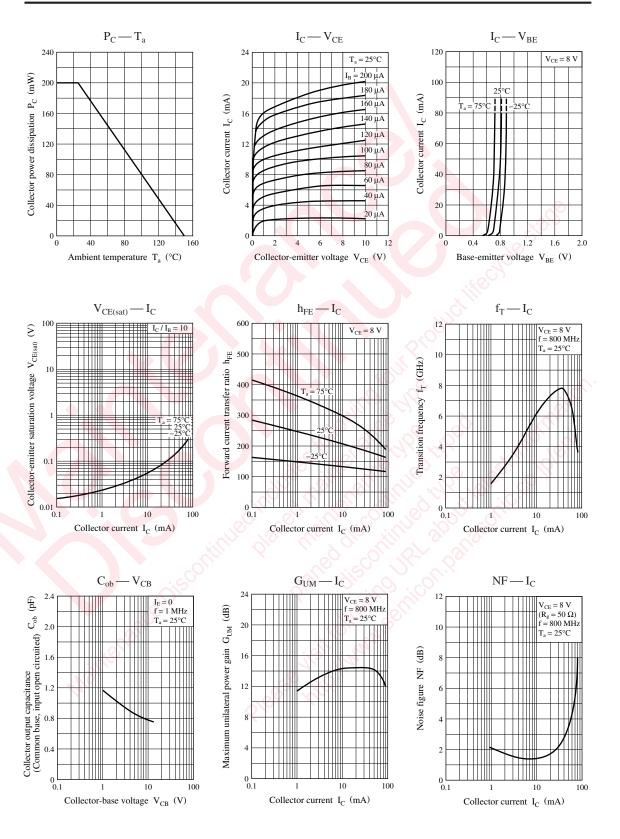
#### Marking Symbol: 3M

#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	15	S		V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 100 \ \mu \text{A}, I_{\rm B} = 0$	10	, v		V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 10 \text{ V}, I_E = 0$	$\sqrt{2}$		1	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 2 V, I_C = 0$			1	μΑ
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 8 V, I_C = 20 mA$	50	150	300	_
Transition frequency	f <sub>T</sub>	$V_{CE} = 8 \text{ V}, I_{C} = 20 \text{ mA}, f = 0.8 \text{ GHz}$	5	6		GHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		0.7	1.2	pF
Forward transfer gain	S <sub>21e</sub>   <sup>2</sup>	$V_{CE} = 8 \text{ V}, I_{C} = 20 \text{ mA}, f = 0.8 \text{ GHz}$	10.0	13.5		dB
Maximum unilateral power gain	G <sub>UM</sub>	$V_{CE} = 8 \text{ V}, I_{C} = 20 \text{ mA}, f = 0.8 \text{ GHz}$		15		dB
Noise figure	NF <	$V_{CE} = 8 \text{ V}, I_C = 20 \text{ mA}, f = 0.8 \text{ GHz}$			2	dB

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

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